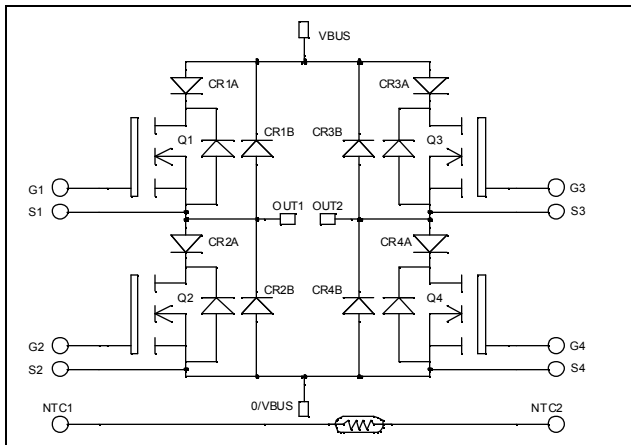


Full bridge
Series & parallel diodes
MOSFET Power Module

$V_{DSS} = 1000V$

$R_{DSon} = 450m\Omega$ typ @ $T_j = 25^\circ C$

$I_D = 18A$ @ $T_c = 25^\circ C$

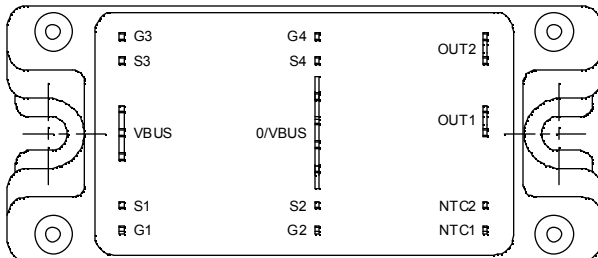


Application

- Motor control
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Power MOS 7[®] MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration



Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	1000	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	18
		$T_c = 80^\circ C$	14
I_{DM}	Pulsed Drain current	72	A
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	540	m Ω
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	357
I_{AR}	Avalanche current (repetitive and non repetitive)	18	A
E_{AR}	Repetitive Avalanche Energy	50	mJ
E_{AS}	Single Pulse Avalanche Energy	2500	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0\text{V}, V_{DS} = 1000\text{V}$			100	μA
		$V_{GS} = 0\text{V}, V_{DS} = 800\text{V}$			500	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 9\text{A}$		450	540	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.5\text{mA}$	3		5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$			± 100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$		4350		pF
C_{oss}	Output Capacitance	$V_{DS} = 25\text{V}$		715		
C_{rss}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		120		
Q_g	Total gate Charge	$V_{GS} = 10\text{V}$		154		nC
Q_{gs}	Gate – Source Charge	$V_{Bus} = 500\text{V}$		26		
Q_{gd}	Gate – Drain Charge	$I_D = 18\text{A}$		97		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C $V_{GS} = 15\text{V}$ $V_{Bus} = 667\text{V}$ $I_D = 18\text{A}$ $R_G = 5\Omega$		10		ns
T_r	Rise Time			12		
$T_{d(off)}$	Turn-off Delay Time			121		
T_f	Fall Time			35		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15\text{V}, V_{Bus} = 667\text{V}$ $I_D = 18\text{A}, R_G = 5\Omega$		639		μJ
E_{off}	Turn-off Switching Energy			380		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15\text{V}, V_{Bus} = 667\text{V}$ $I_D = 18\text{A}, R_G = 5\Omega$		1046		μJ
E_{off}	Turn-off Switching Energy			451		

Series diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		200			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 200\text{V}$	$T_j = 25^\circ\text{C}$		250	μA
			$T_j = 125^\circ\text{C}$		500	
I_F	DC Forward Current			30		A
V_F	Diode Forward Voltage	$I_F = 30\text{A}$		1.1	1.15	V
		$I_F = 60\text{A}$		1.4		
		$I_F = 30\text{A}$	$T_j = 125^\circ\text{C}$		0.9	
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}$ $V_R = 133\text{V}$ $di/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		24	ns
			$T_j = 125^\circ\text{C}$		48	
Q_{rr}	Reverse Recovery Charge	$I_F = 30\text{A}$ $V_R = 133\text{V}$ $di/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		33	nC
			$T_j = 125^\circ\text{C}$		150	

Parallel diode ratings and characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			1000			V
I _{RM}	Maximum Reverse Leakage Current	V _R =1000V	T _j = 25°C			250	μA
			T _j = 125°C			500	
I _F	DC Forward Current	T _c = 65°C			30		A
V _F	Diode Forward Voltage	I _F = 30A			1.9	2.3	V
		I _F = 60A			2.2		
		I _F = 30A	T _j = 125°C		1.7		
t _{rr}	Reverse Recovery Time	I _F = 30A V _R = 667V di/dt = 200A/μs	T _j = 25°C		290		ns
			T _j = 125°C		390		
Q _{rr}	Reverse Recovery Charge			T _j = 25°C		670	nC
				T _j = 125°C		2350	

Thermal and package characteristics

<i>Symbol</i>	<i>Characteristic</i>			<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
R _{thJC}	Junction to Case Thermal Resistance	Transistor				0.35	°C/W
		Diode				1.2	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, I _{isol} < 1mA, 50/60Hz			2500			V
T _J	Operating junction temperature range			-40		150	°C
T _{STG}	Storage Temperature Range			-40		125	
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight					160	g

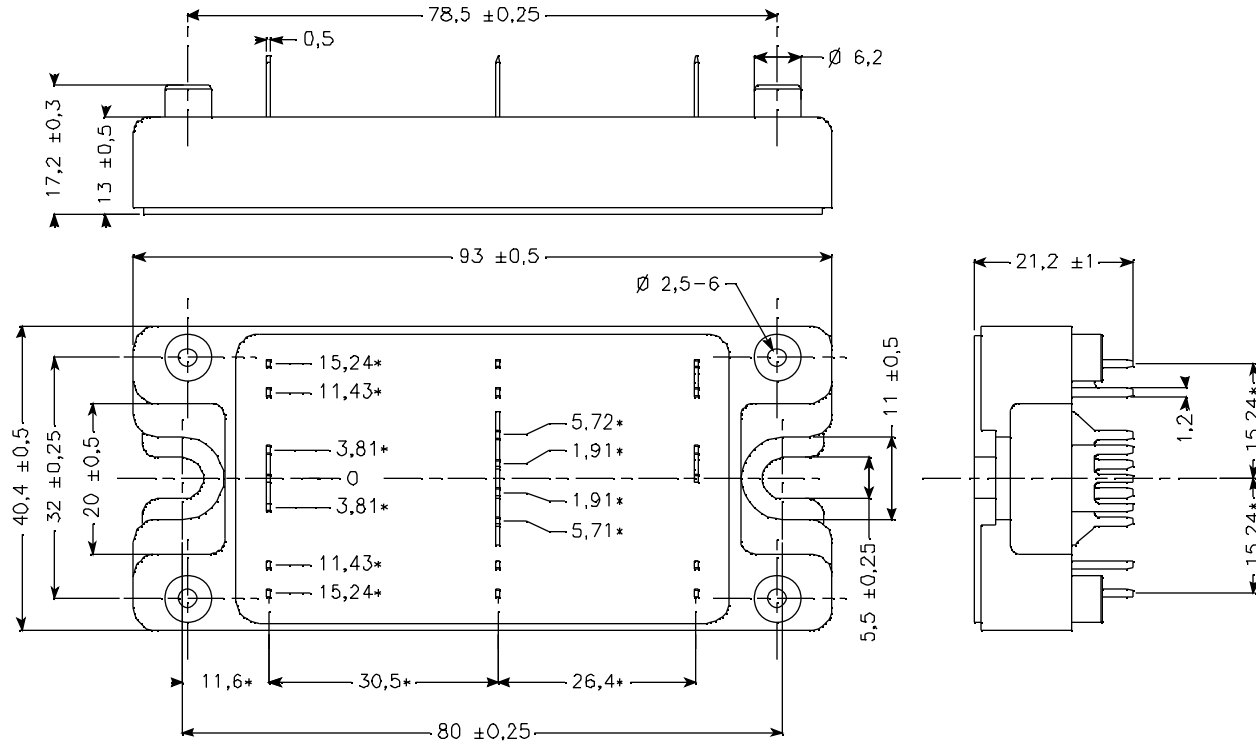
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

<i>Symbol</i>	<i>Characteristic</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
R ₂₅	Resistance @ 25°C		50		kΩ
B _{25/85}	T ₂₅ = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

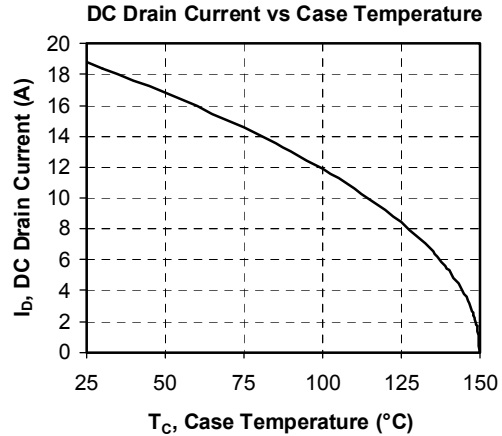
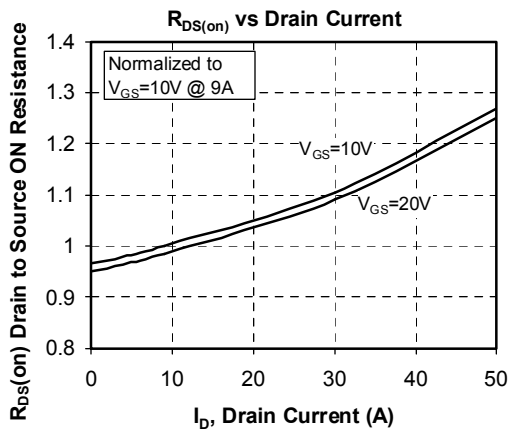
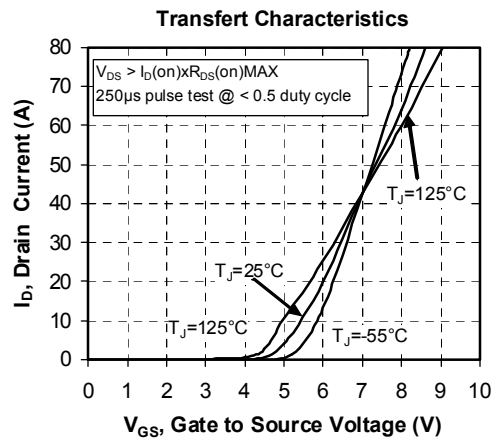
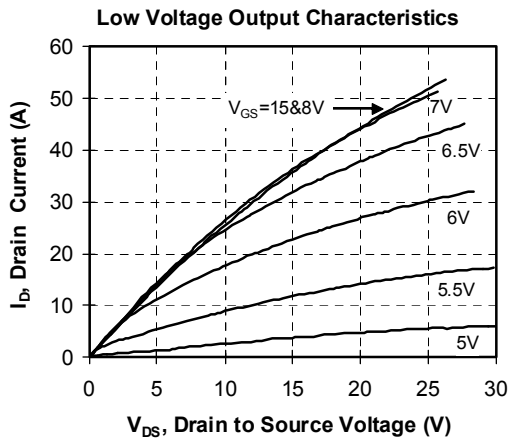
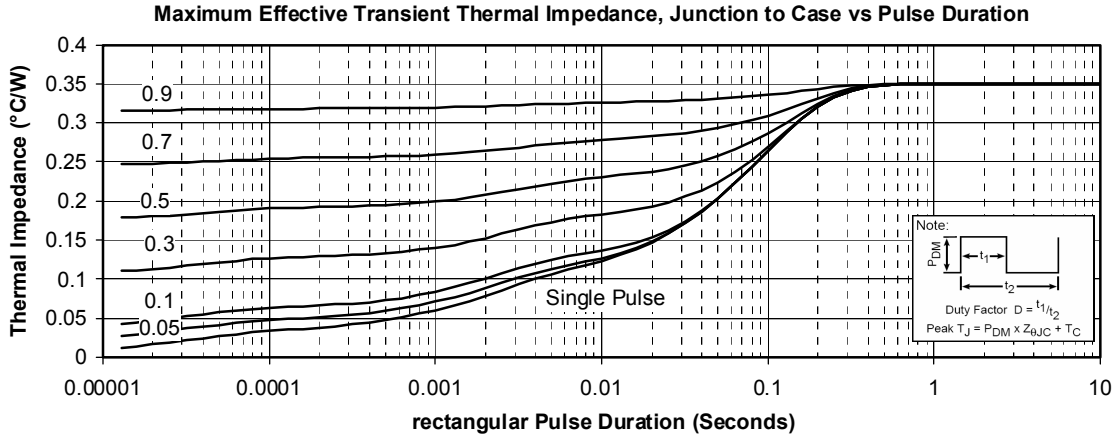
SP4 Package outline (dimensions in mm)

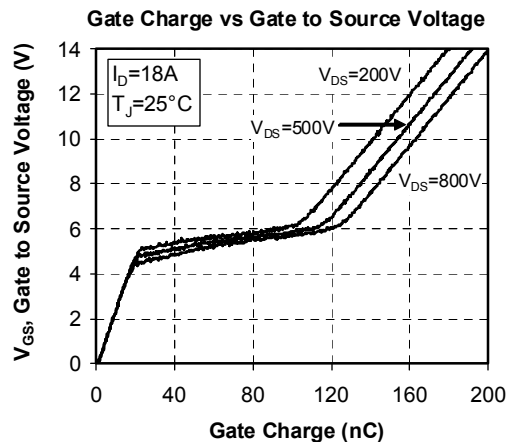
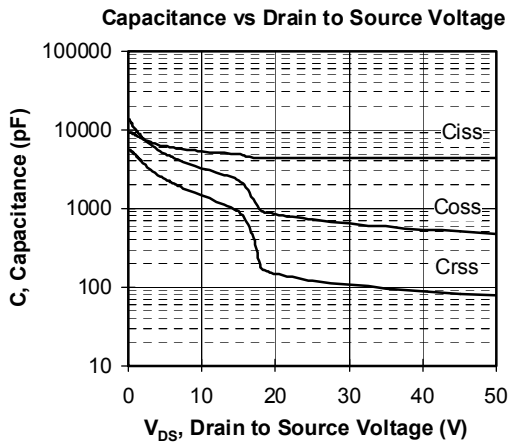
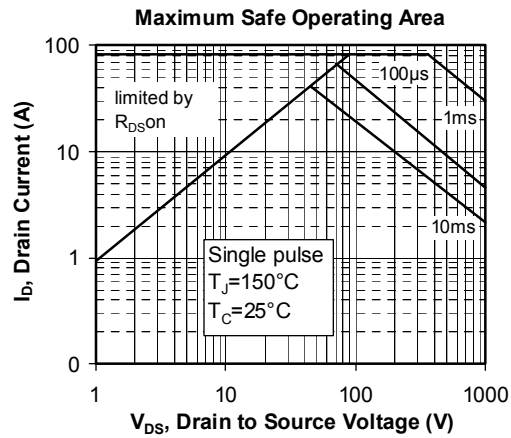
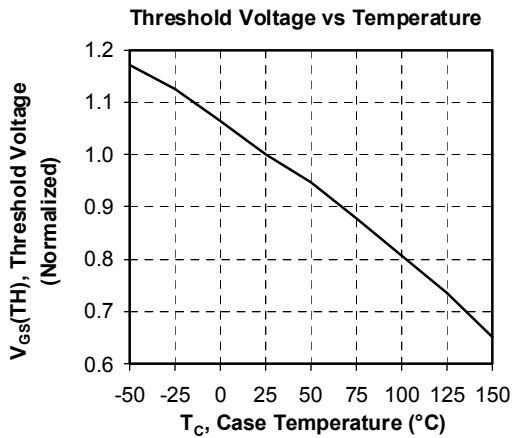
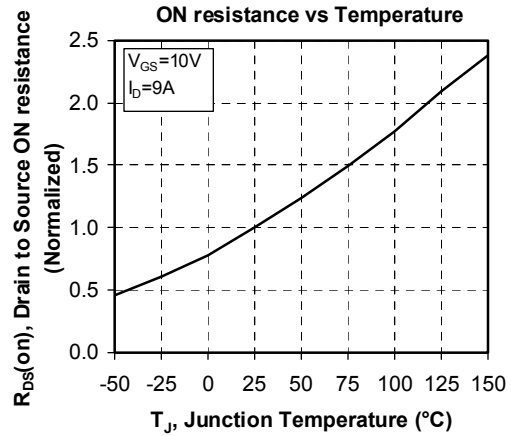
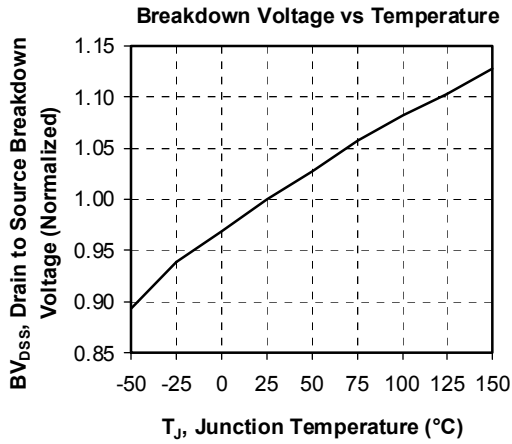


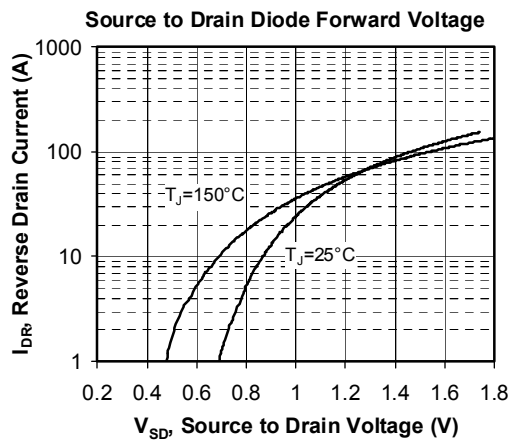
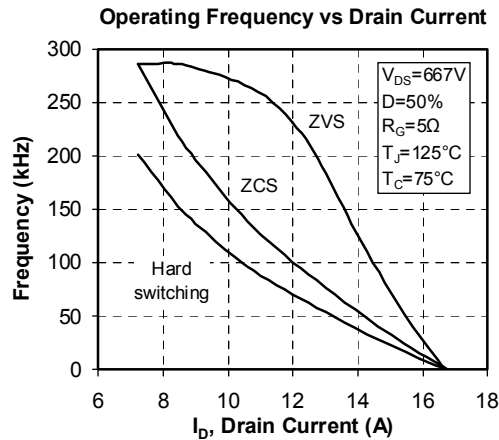
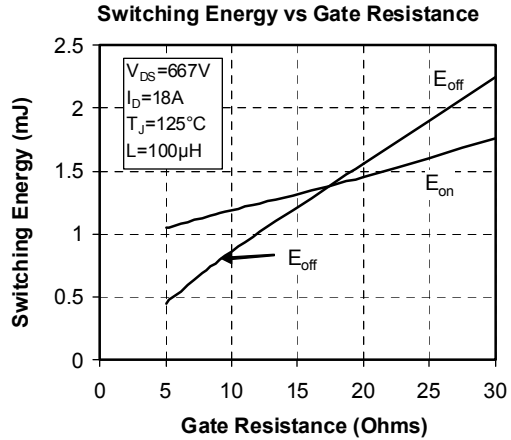
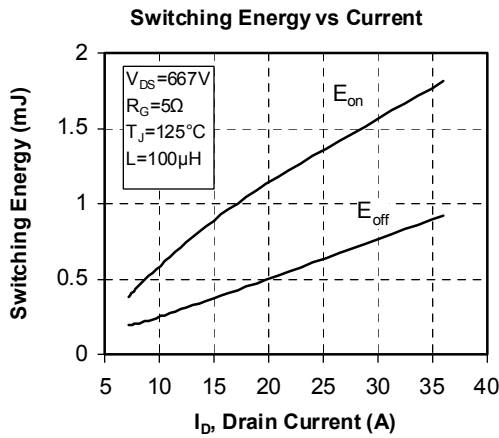
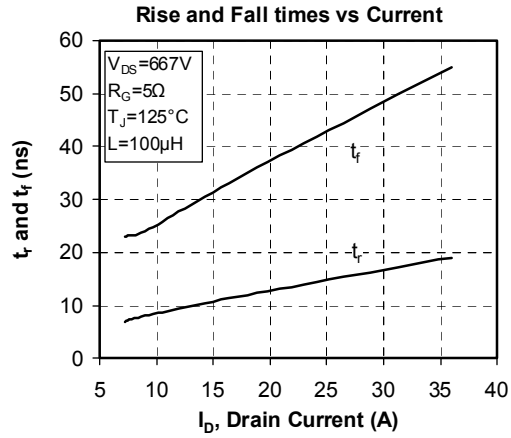
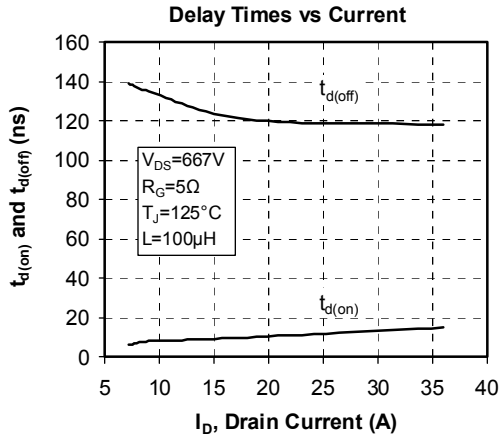
ALL DIMENSIONS MARKED "*" ARE TOLERANCED AS : $\varnothing 1$

See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

Typical Performance Curve







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